

OKI semiconductor

MSM2716AS

16384-BIT UV ERASABLE ELECTRICALLY PROGRAMMABLE
READ-ONLY MEMORY

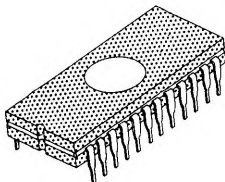
GENERAL DESCRIPTION

The MSM2716AS is a read only memory with the capacity of 2048 words x 8 bits whose contents can be erased by ultraviolet ray irradiation. Since the memory contents can be programmed as desired by the user and the alteration is easy, it is ideal for a processor program.

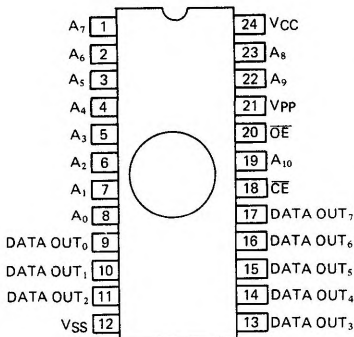
The MSM2716AS is processed as the N-channel silicon gate MOS with floating gates, and is encased in a standard 24-pin ceramic package.

FEATURES

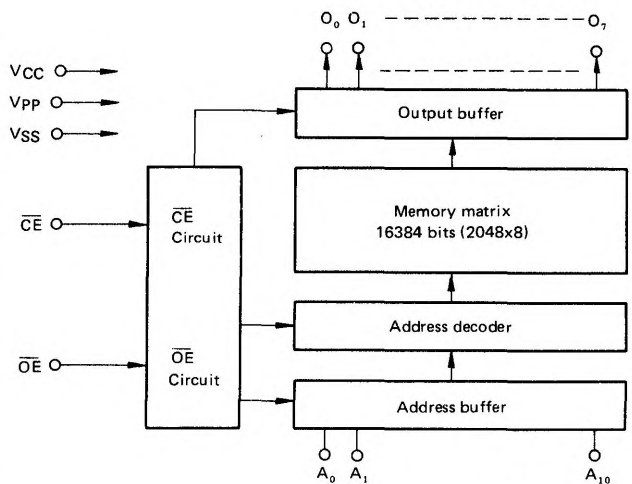
- Single power supply +5V
- Low power Dissipation 525 mW in operation and 132 mW in standby state
- UV erasable and electrically programmable.
- Minimum programming time 100 seconds for all 16,384 bits.
- Full decoding 2048 words x 8 bits
- Static operation No clock requirement
- TTL connection for inputs/outputs (tristate output)
- Easy expansion of memory capacity (wired-OR connection)
- Access time 450 ns
- Pin compatible with INTEL's 2716



PIN CONFIGURATION



FUNCTIONAL BLOCK DIAGRAM



The specifications are subject to change without notice.

FUNCTION TABLE

Mode \ Pins	\overline{CE} (18)	\overline{OE} (20)	V _{pp} (21)	V _{cc} (24)	OUTPUTS (9~11, 13~17)
Read	V _{IL}	V _{IL}	+5V	+5V	D out
Stand by	V _{IH}	Don't care	+5V	+5V	High Z
Program	Pulsed V _{IL} to V _{IH}	V _{IH}	+25V	+5V	D in
Program Verify	V _{IL}	V _{IL}	+25V	+5V	D out
Program Inhibit	V _{IL}	V _{IH}	+25V	+5V	High Z

High Z = High Impedance

ELECTRICAL CHARACTERISTICS ABSOLUTE MAXIMUM RATING

Item	Symbol	Conditions	Rated Value	Unit
Storage Temperature	T _{stg}	—	-55 to +125	°C
Terminal Voltage Address Input and Data Input Program Input V _{pp} V _{cc}			(to V _{ss}) -0.3 to +6 -0.3 to +28 -0.3 to +6	V
Power Dissipation	P _D		525	mW

READ OPERATION

Operating range (for V_{ss} = 0V)

Item	Symbol	Conditions	Guaranteed Range	Unit
Source Supply Voltage	V _{cc}		+5 to ±0.25	V
	V _{pp}		V _{cc} ± 0.6	V
Operating Temperature	T _{opr}		0 to +70	°C
Number of Leads	N	TTL gate load	1	—

DC OPERATING CHARACTERISTICS

($V_{CC} = 5V \pm 5\%$, $V_{pp} = V_{CC} \pm 0.6V$, $T_a = 0^\circ C$ to $+70^\circ C$ unless specified otherwise)

Item	Symbol	Conditions	Guaranteed Range			Unit
			Min.	Typ.	Max.	
Input Leak Current	I_{LI}	$V_{IN} = 5.25V$			10	μA
Output Leak Current	I_{LO}	$V_{OUT} = 5.25V$			10	μA
Program Pin Current	I_{pp}	$V_{pp} = 5.85V$			5	mA
Collector Supply Current (Standby)	I_{CC1}	$\overline{CE} = V_{IH}, \overline{OE} = V_{IL}$		10	25	mA
Collector Supply Current (Active)	I_{CC2}	$\overline{OE} = \overline{CE} = V_{IL}$		60	100	mA
"H" Input Voltage	V_{IH}		2.2		$V_{CC}+1$	V
"L" Input Voltage	V_{IL}		-0.1		0.8	V
"H" Output Voltage	V_{OH}	$I_{OH} = -400 \mu A$	2.4			V
"L" Output Voltage	V_{OL}	$I_{OL} = 2.1 mA$			0.45	V

Note: V_{CC} must be supplied before or when V_{pp} is supplied, and must be cut off when or after V_{pp} is cut off.

AC OPERATING CHARACTERISTICS

($V_{CC} = 5V \pm 5\%$, $V_{pp} = V_{CC} \pm 0.6V$, $T_a = 0^\circ C$ to $+70^\circ C$ unless specified otherwise)

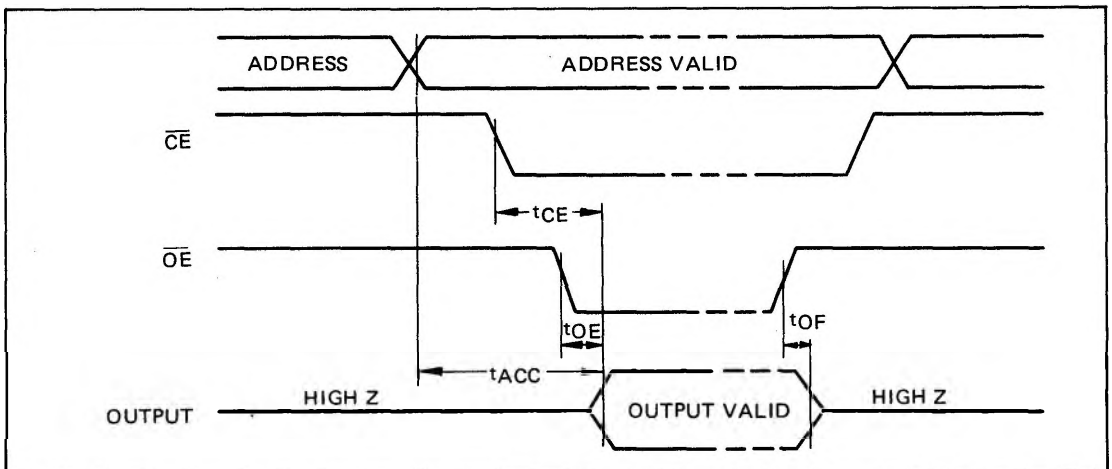
Item	Symbol	Conditions	Guaranteed range			Unit
			Min.	Typ.	Max.	
Address Output Delay Time	t_{ACC}	$\overline{OE} = CE = V_{IL}$		250	450	ns
\overline{CE} Output Delay Time	t_{CE}	$\overline{OE} = V_{IL}$		280	450	ns
\overline{OE} Output Delay Time	t_{OE}	$\overline{CE} = V_{IL}$			120	ns
Output Disable Delay Time	t_{DF}	$\overline{CE} = V_{IL}$	0		100	ns

*AC characteristics measuring conditions

- Input pulse level 0.8 ~ 2.2V
- Input rise/fall time Within 20 ns
- Output load 1TTL Gate + 100 pF
- Timing measurement reference levels Input 1V and 2V, Output 0.8V and 2.4V

TIME CHART

Read Mode



PROGRAMMING OPERATION

($V_{CC} = 5V \pm 5\%$, $V_{pp} = 25V \pm 1V$, $T_a = 25^\circ C \pm 5^\circ C$ unless specified otherwise)

Item	Symbol	Conditions	Guaranteed Range			Unit
			Min.	Typ.	Max.	
Input Leak Current	I_{LI}	$V_{IN} = 5.25V/0.45V$			10	μA
Program Pin Current	I_{pp1}	$\overline{CE} = V_{IL}$			6	mA
Programming Current	I_{pp2}	$\overline{CE} = V_{IH}$			30	mA
Collector Supply Current	I_{CC}				100	mA
"H" Input Voltage	V_{IH}		2.2		$V_{CC}+1$	V
"L" Input Voltage	V_{IL}		-0.1		0.8	V

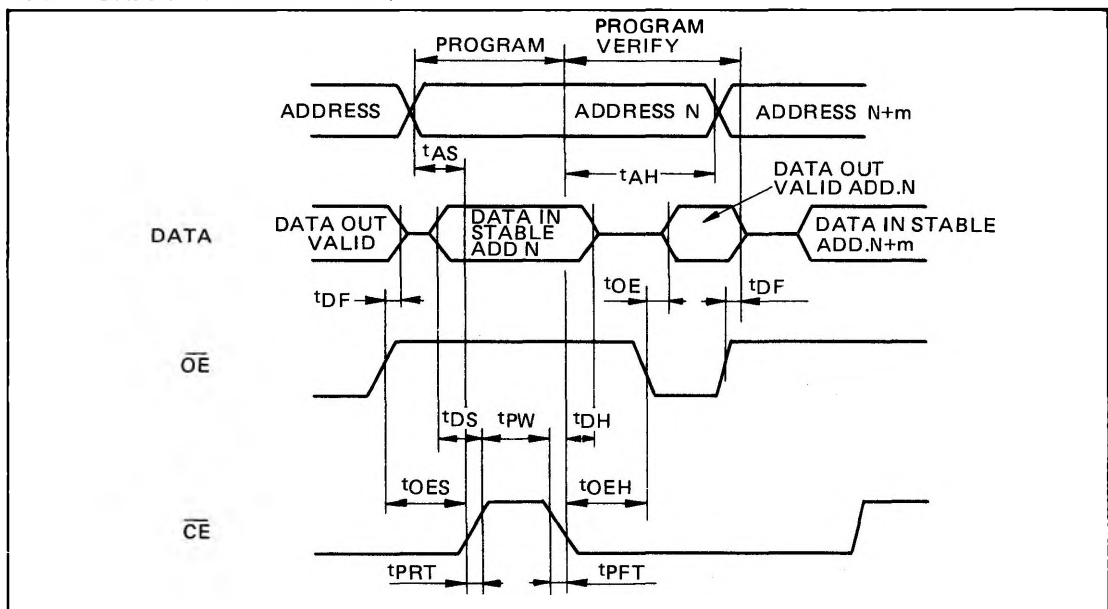
AC CHARACTERISTICS

($V_{CC} = 5V \pm 5\%$, $V_{pp} = 25V \pm 1V$, $T_a = 25^\circ C \pm 5^\circ C$ unless specified otherwise)

Item	Symbol	Guaranteed Range			Unit
		Min.	Typ.	Max.	
Address Setup Time	t_{AS}	2			μS
OE Setup Time	t_{OES}	2			μS
Data Setup Time	t_{DS}	2			μS
Address Hold Time	t_{AH}	2			μS
OE Hold Time	t_{OEh}	2			μS
Data Hold Time	t_{DH}	2			μS
Output Disable Delay Time	t_{DF}	0		120	ns
Output Enable Delay Time	t_{OE}			120	ns
Program Pulse Width	t_{PW}	45	50	55	ms
Program Pulse Fall Time	t_{PRT}	5			ns
Program Pulse Rise Time	t_{PFT}	5			ns

* AC characteristics measurement conditions are the same as those for read operation.

TIME CHART (PROGRAM MODE)



OPERATION

● Read mode

When \overline{OE} is set to "L" level, reading of the memory contents starts 450 ns (T_{ACC}) after the address or 120 ns (t_{OE}) after \overline{OE} if the address is already fixed.

● Output deselection

Multiple MSM2716AS chips may be combined by wired-OR connection. The data in one MSM2716AS is read when \overline{OE} is at "L" level. Other MSM2716AS chips are set to the output deselection state by setting the \overline{OE} to the "H" level.

● Standby mode

Setting \overline{CE} to "H" level causes the power to be decreased to 1/4 of that in the read mode (525 mW → 132 mW).

● Programming

All bits of the MSM2716AS are set to "H" level at the time of delivery or after erasure. When 0 is written, the corresponding bit goes to "L" level. In the programming mode, \overline{OE} input at $V_{pp}=25V$ is used as "H" level.

The programming data must be supplied in parallel to output pins ($O_0 \sim O_7$). The address and input are both TTL level. Supplying \overline{CE} input (TTL "H" level) at 50 ms intervals after setting up the address and data enables programming. Avoid programming by supplying a DC signal to \overline{CE} pin.

● Program verify

The MSM2716AS can be verified in the programming mode. V_{pp} for this operation is 25V.

● Program inhibit

Multiple MSM2716AS chips can be programmed in parallel and with different data in this mode. All pins other than \overline{CE} can be used in common for all chips.

Supply TTL "H" level to \overline{CE} pins of the chips to be programmed and TTL "L" level to \overline{CE} pins of the chips not to be programmed.

HANDLING OF MSM2716AS

Since the MSM2716AS is an EPROM of N-channel silicon gate FAMOS type, pay special attention as follows in addition to general handling caution of MOS ICs so as to maintain high reliability.

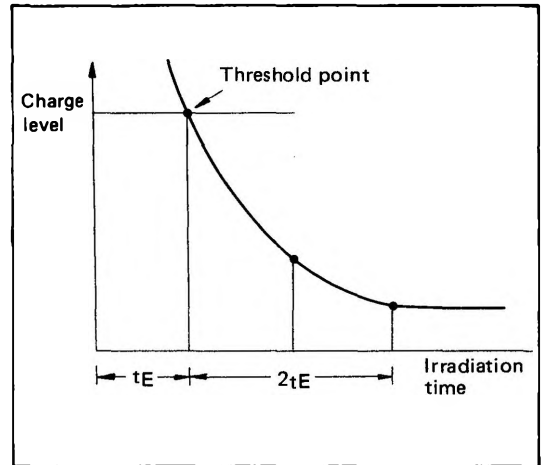
● Attention during writing

Since all bits of the MSM2716AS are erased before delivery, writing can be started as it is. Sufficient erasure is necessary before reprogramming.

For writing operation, avoid a location with strong light intensity. 100–200 lux is allowable.

● Attention during erasure

The contents of the MSM2716AS can be erased by irradiation of ultraviolet rays. The charge (electrons) in the floating gates decreases with the time lapse, but erasing time t_E till the threshold point (where all bits are judged as 1 by a writer) is insufficient. Irradiate for another $2t_E$ for sufficient discharge of electrons.



The irradiation energy for erasure of the MSM2716AS contents is $15W\text{-sec}/\text{cm}^2$.

● Caution for handling

- (1) Keep away from carpet or cloth that generates static electricity.
- (2) Perfectly ground the using writer and the system in which the MSM2716AS is used.
- (3) If a soldering iron is used, be sure to ground it.
- (4) Always carry in electrically conductive plastic mat.
- (5) The programmed ROM must be encased in electrically conductive plastic mat.
- (6) Do not touch the glass seal portion with a hand to prevent insufficient erasure caused by decreased UV ray transmission.

● Caution for system debugging

Check the functioning status by fluctuating the voltage by $\pm 5\%$.